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(FILE 'USPAT' ENTERED AT 16:22:14 ON 31 JAN 1999)
L1 500 S AMORPHOUS(W)SILICON(W)CARBIDE
L2 2 S L1 AND MEMORY CELL
L3 2 S L2 AND SUBSTRATE

=> d cit ab 1-2

1. 5,846,859, Dec. 8, 1998, Method for manufacturing a semiconductor memory device having capacitive storage; Sang-in Lee, 438/253; 148/DIG.148; 438/240, 254 [IMAGE AVAILABLE]

US PAT NO: 5,846,859 [IMAGE AVAILABLE] L3: 1 of 2

ABSTRACT:
A capacitor in a semiconductor device having a dielectric film formed of high dielectric material and a manufacturing method therefor are provided. The capacitor consists of electrodes including a dielectric film and an amorphous SiC layer. Thus, the diffusion of oxygen atoms through a grain boundary into an underlayer and the formation of an oxide
layer on the surface of the SiC layer can both be prevented, providing for a highly reliable capacitor electrode and an equivalent oxide thickness which is no thicker than required.

2. 5,738,731, Apr. 14, 1998, Photovoltaic device; Masahiro Shindo, et al. 136/249, 260, 262; 257/184, 440 [IMAGE AVAILABLE]

US PAT NO: 5,738,731 [IMAGE AVAILABLE] L3: 2 of 2

ABSTRACT:
A solar cell comprising:
a first junction part having a first conductivity type first semiconductor film and a second conductivity type second semiconductor film formed on an upper surface of said first semiconductor film; and
a second junction part having a first conductivity type third semiconductor film formed on an upper surface of said second semiconductor film and a second conductivity type fourth semiconductor formed on an upper surface of said third semiconductor film,
said junction parts arranged from that having a larger forbidden band width along the direction of progress of light through said semiconductor layers,
said first, second, third, and fourth semiconductor films being formed of single-crystalline filming;
wherein an interlayer conductor prepared from a metal forming ohmic junctions with each of said junction parts and having a thickness capable of transmitting light therethrough is interposed between said first and second junction parts; and

wherein said second semiconductor film arranged on one side of said interlayer conductor is different in crystal orientation from said third semiconductor film arranged on the other side of said interlayer conductor.